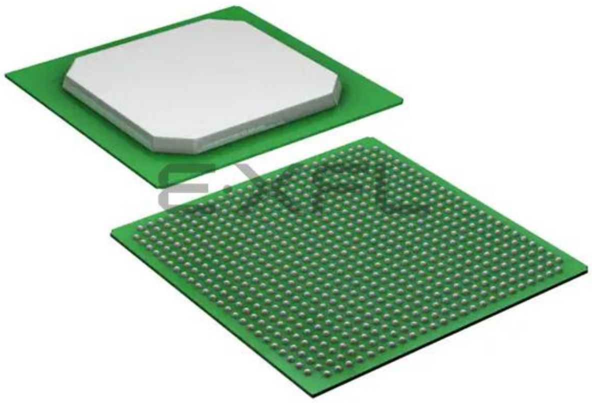
Intel - EP4CGX75DF27I7N Datasheet



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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Active
Number of LABs/CLBs	4620
Number of Logic Elements/Cells	73920
Total RAM Bits	4257792
Number of I/O	310
Number of Gates	-
Voltage - Supply	1.16V ~ 1.24V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	672-BGA
Supplier Device Package	672-FBGA (27x27)
Purchase URL	https://www.e-xfl.com/product-detail/intel/ep4cgx75df27i7n

Email: info@E-XFL.COM Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

☞ Cyclone IV E industrial devices I7 are offered with extended operating temperature range.

Absolute Maximum Ratings

Absolute maximum ratings define the maximum operating conditions for Cyclone IV devices. The values are based on experiments conducted with the device and theoretical modeling of breakdown and damage mechanisms. The functional operation of the device is not implied at these conditions. Table 1–1 lists the absolute maximum ratings for Cyclone IV devices.

CAUTION Conditions beyond those listed in Table 1–1 cause permanent damage to the device. Additionally, device operation at the absolute maximum ratings for extended periods of time have adverse effects on the device.

Table 1–1. Absolute Maximum Ratings for Cyclone IV Devices *(1)*

Symbol	Parameter	Min	Max	Unit
V_{CCINT}	Core voltage, PCI Express® (PCIe®) hard IP block, and transceiver physical coding sublayer (PCS) power supply	–0.5	1.8	V
V_{CCA}	Phase-locked loop (PLL) analog power supply	–0.5	3.75	V
V_{CCD_PLL}	PLL digital power supply	–0.5	1.8	V
V_{CCIO}	I/O banks power supply	–0.5	3.75	V
V_{CC_CLKIN}	Differential clock input pins power supply	–0.5	4.5	V
V_{CCH_GXB}	Transceiver output buffer power supply	–0.5	3.75	V
V_{CCA_GXB}	Transceiver physical medium attachment (PMA) and auxiliary power supply	–0.5	3.75	V
V_{CCL_GXB}	Transceiver PMA and auxiliary power supply	–0.5	1.8	V
V_I	DC input voltage	–0.5	4.2	V
I_{OUT}	DC output current, per pin	–25	40	mA
T_{STG}	Storage temperature	–65	150	°C
T_J	Operating junction temperature	–40	125	°C

Note to Table 1–1:

(1) Supply voltage specifications apply to voltage readings taken at the device pins with respect to ground, not at the power supply.

Maximum Allowed Overshoot or Undershoot Voltage

During transitions, input signals may overshoot to the voltage shown in Table 1–2 and undershoot to –2.0 V for a magnitude of currents less than 100 mA and for periods shorter than 20 ns. Table 1–2 lists the maximum allowed input overshoot voltage and the duration of the overshoot voltage as a percentage over the lifetime of the device. The maximum allowed overshoot duration is specified as a percentage of high-time over the lifetime of the device.

Table 1–3. Recommended Operating Conditions for Cyclone IV E Devices (1), (2) (Part 2 of 2)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
I_{Diode}	Magnitude of DC current across PCI-clamp diode when enable	—	—	—	10	mA

Notes to Table 1–3:

(1) Cyclone IV E 1.0 V core voltage devices only support C8L, C9L, and I8L speed grades. Cyclone IV E 1.2 V core voltage devices only support C6, C7, C8, I7, and A7 speed grades.

(2) V_{CCIO} for all I/O banks must be powered up during device operation. All `VCCA` pins must be powered to 2.5 V (even when PLLs are not used) and must be powered up and powered down at the same time.

(3) V_{CC} must rise monotonically.

(4) V_{CCIO} powers all input buffers.

(5) The POR time for Standard POR ranges between 50 and 200 ms. Each individual power supply must reach the recommended operating range within 50 ms.

(6) The POR time for Fast POR ranges between 3 and 9 ms. Each individual power supply must reach the recommended operating range within 3 ms.

Table 1–4. Recommended Operating Conditions for Cyclone IV GX Devices (Part 1 of 2)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{CCINT} (3)	Core voltage, PCIe hard IP block, and transceiver PCS power supply	—	1.16	1.2	1.24	V
V_{CCA} (1), (3)	PLL analog power supply	—	2.375	2.5	2.625	V
V_{CCD_PLL} (2)	PLL digital power supply	—	1.16	1.2	1.24	V
V_{CCIO} (3), (4)	I/O banks power supply for 3.3-V operation	—	3.135	3.3	3.465	V
	I/O banks power supply for 3.0-V operation	—	2.85	3	3.15	V
	I/O banks power supply for 2.5-V operation	—	2.375	2.5	2.625	V
	I/O banks power supply for 1.8-V operation	—	1.71	1.8	1.89	V
	I/O banks power supply for 1.5-V operation	—	1.425	1.5	1.575	V
	I/O banks power supply for 1.2-V operation	—	1.14	1.2	1.26	V
V_{CC_CLKIN} (3), (5), (6)	Differential clock input pins power supply for 3.3-V operation	—	3.135	3.3	3.465	V
	Differential clock input pins power supply for 3.0-V operation	—	2.85	3	3.15	V
	Differential clock input pins power supply for 2.5-V operation	—	2.375	2.5	2.625	V
	Differential clock input pins power supply for 1.8-V operation	—	1.71	1.8	1.89	V
	Differential clock input pins power supply for 1.5-V operation	—	1.425	1.5	1.575	V
	Differential clock input pins power supply for 1.2-V operation	—	1.14	1.2	1.26	V
V_{CCH_GXB}	Transceiver output buffer power supply	—	2.375	2.5	2.625	V

Table 1–4. Recommended Operating Conditions for Cyclone IV GX Devices (Part 2 of 2)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{CCA_GXB}	Transceiver PMA and auxiliary power supply	—	2.375	2.5	2.625	V
V_{CCL_GXB}	Transceiver PMA and auxiliary power supply	—	1.16	1.2	1.24	V
V_I	DC input voltage	—	–0.5	—	3.6	V
V_O	DC output voltage	—	0	—	V_{CCIO}	V
T_J	Operating junction temperature	For commercial use	0	—	85	°C
		For industrial use	–40	—	100	°C
t_{RAMP}	Power supply ramp time	Standard power-on reset (POR) *(7)*	50 µs	—	50 ms	—
		Fast POR *(8)*	50 µs	—	3 ms	—
I_{Diode}	Magnitude of DC current across PCI-clamp diode when enabled	—	—	—	10	mA

Notes to Table 1–4:

(1) All `VCCA` pins must be powered to 2.5 V (even when PLLs are not used) and must be powered up and powered down at the same time.

(2) You must connect V_{CCD_PLL} to V_{CCINT} through a decoupling capacitor and ferrite bead.

(3) Power supplies must rise monotonically.

(4) V_{CCIO} for all I/O banks must be powered up during device operation. Configurations pins are powered up by V_{CCIO} of I/O Banks 3, 8, and 9 where I/O Banks 3 and 9 only support V_{CCIO} of 1.5, 1.8, 2.5, 3.0, and 3.3 V. For fast passive parallel (FPP) configuration mode, the V_{CCIO} level of I/O Bank 8 must be powered up to 1.5, 1.8, 2.5, 3.0, and 3.3 V.

(5) You must set V_{CC_CLKIN} to 2.5 V if you use `CLKIN` as a high-speed serial interface (HSSI) `refclk` or as a `DIFFCLK` input.

(6) The `CLKIN` pins in I/O Banks 3B and 8B can support single-ended I/O standard when the pins are used to clock left PLLs in non-transceiver applications.

(7) The POR time for Standard POR ranges between 50 and 200 ms. V_{CCINT}, V_{CCA}, and V_{CCIO} of I/O Banks 3, 8, and 9 must reach the recommended operating range within 50 ms.

(8) The POR time for Fast POR ranges between 3 and 9 ms. V_{CCINT}, V_{CCA}, and V_{CCIO} of I/O Banks 3, 8, and 9 must reach the recommended operating range within 3 ms.

ESD Performance

This section lists the electrostatic discharge (ESD) voltages using the human body model (HBM) and charged device model (CDM) for Cyclone IV devices general purpose I/Os (GPIOs) and high-speed serial interface (HSSI) I/Os. Table 1–5 lists the ESD for Cyclone IV devices GPIOs and HSSI I/Os.

Table 1–5. ESD for Cyclone IV Devices GPIOs and HSSI I/Os

Symbol	Parameter	Passing Voltage	Unit
V_{ESDHBM}	ESD voltage using the HBM (GPIOs) *(1)*	± 2000	V
	ESD using the HBM (HSSI I/Os) *(2)*	± 1000	V
V_{ESDCDM}	ESD using the CDM (GPIOs)	± 500	V
	ESD using the CDM (HSSI I/Os) *(2)*	± 250	V

Notes to Table 1–5:

(1) The passing voltage for EP4CGX15 and EP4CGX30 row I/Os is ±1000V.

(2) This value is applicable only to Cyclone IV GX devices.

DC Characteristics

This section lists the I/O leakage current, pin capacitance, on-chip termination (OCT) tolerance, and bus hold specifications for Cyclone IV devices.

Supply Current

The device supply current requirement is the minimum current drawn from the power supply pins that can be used as a reference for power size planning. Use the Excel-based early power estimator (EPE) to get the supply current estimates for your design because these currents vary greatly with the resources used. Table 1–6 lists the I/O pin leakage current for Cyclone IV devices.

Table 1–6. I/O Pin Leakage Current for Cyclone IV Devices *(1), (2)*

Symbol	Parameter	Conditions	Device	Min	Typ	Max	Unit
I_I	Input pin leakage current	V_I = 0 V to $V_{CCIOMAX}$	—	–10	—	10	µA
I_{OZ}	Tristated I/O pin leakage current	V_O = 0 V to $V_{CCIOMAX}$	—	–10	—	10	µA

Notes to Table 1–6:

(1) This value is specified for normal device operation. The value varies during device power-up. This applies for all V_{CCIO} settings (3.3, 3.0, 2.5, 1.8, 1.5, and 1.2 V).

(2) The 10 µA I/O leakage current limit is applicable when the internal clamping diode is off. A higher current can be observed when the diode is on.

Bus Hold

The bus hold retains the last valid logic state after the source driving it either enters the high impedance state or is removed. Each I/O pin has an option to enable bus hold in user mode. Bus hold is always disabled in configuration mode.

Table 1–7 lists bus hold specifications for Cyclone IV devices.

Table 1–7. Bus Hold Parameter for Cyclone IV Devices (Part 1 of 2) *(1)*

Parameter	Condition	V_{CCIO} (V)												Unit
		1.2		1.5		1.8		2.5		3.0		3.3		
		Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
Bus hold low, sustaining current	$V_{IN} > V_{IL}$ (maximum)	8	—	12	—	30	—	50	—	70	—	70	—	µA
Bus hold high, sustaining current	$V_{IN} < V_{IL}$ (minimum)	–8	—	–12	—	–30	—	–50	—	–70	—	–70	—	µA
Bus hold low, overdrive current	$0 V < V_{IN} < V_{CCIO}$	—	125	—	175	—	200	—	300	—	500	—	500	µA
Bus hold high, overdrive current	$0 V < V_{IN} < V_{CCIO}$	—	–125	—	–175	—	–200	—	–300	—	–500	—	–500	µA

Table 1–7. Bus Hold Parameter for Cyclone IV Devices (Part 2 of 2) *(1)*

Parameter	Condition	V_{CCIO} (V)												Unit
		1.2		1.5		1.8		2.5		3.0		3.3		
		Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
Bus hold trip point	—	0.3	0.9	0.375	1.125	0.68	1.07	0.7	1.7	0.8	2	0.8	2	V

Note to Table 1–7:

(1) Bus hold trip points are based on the calculated input voltages from the JEDEC standard.

OCT Specifications

Table 1–8 lists the variation of OCT without calibration across process, temperature, and voltage (PVT).

Table 1–8. Series OCT Without Calibration Specifications for Cyclone IV Devices

Description	V_{CCIO} (V)	Resistance Tolerance		Unit
		Commercial Maximum	Industrial, Extended industrial, and Automotive Maximum	
Series OCT without calibration	3.0	±30	±40	%
	2.5	±30	±40	%
	1.8	±40	±50	%
	1.5	±50	±50	%
	1.2	±50	±50	%

OCT calibration is automatically performed at device power-up for OCT-enabled I/Os.

Table 1–9 lists the OCT calibration accuracy at device power-up.

Table 1–9. Series OCT with Calibration at Device Power-Up Specifications for Cyclone IV Devices

Description	V_{CCIO} (V)	Calibration Accuracy		Unit
		Commercial Maximum	Industrial, Extended industrial, and Automotive Maximum	
Series OCT with calibration at device power-up	3.0	±10	±10	%
	2.5	±10	±10	%
	1.8	±10	±10	%
	1.5	±10	±10	%
	1.2	±10	±10	%

The OCT resistance may vary with the variation of temperature and voltage after calibration at device power-up. Use Table 1–10 and Equation 1–1 to determine the final OCT resistance considering the variations after calibration at device power-up. Table 1–10 lists the change percentage of the OCT resistance with voltage and temperature.

Table 1–10. OCT Variation After Calibration at Device Power-Up for Cyclone IV Devices

Nominal Voltage	dR/dT (%/°C)	dR/dV (%/mV)
3.0	0.262	–0.026
2.5	0.234	–0.039
1.8	0.219	–0.086
1.5	0.199	–0.136
1.2	0.161	–0.288

Equation 1–1. Final OCT Resistance *(1), (2), (3), (4), (5), (6)*

$\Delta R_V = (V_2 - V_1) \times 1000 \times dR/dV$ ——— *(7)*

$\Delta R_T = (T_2 - T_1) \times dR/dT$ ——— *(8)*

For $\Delta R_x < 0$; $MF_x = 1/ (|\Delta R_x|/100 + 1)$ ——— *(9)*

For $\Delta R_x > 0$; $MF_x = \Delta R_x/100 + 1$ ——— *(10)*

$MF = MF_V \times MF_T$ ——— *(11)*

$R_{final} = R_{initial} \times MF$ ——— *(12)*

Notes to Equation 1–1:

(1) T_2 is the final temperature.
(2) T_1 is the initial temperature.
(3) MF is multiplication factor.
(4) R_{final} is final resistance.
(5) $R_{initial}$ is initial resistance.
(6) Subscript $_x$ refers to both $_V$ and $_T$.
(7) ΔR_V is a variation of resistance with voltage.
(8) ΔR_T is a variation of resistance with temperature.
(9) dR/dT is the change percentage of resistance with temperature after calibration at device power-up.
(10) dR/dV is the change percentage of resistance with voltage after calibration at device power-up.
(11) V_2 is final voltage.
(12) V_1 is the initial voltage.

Internal Weak Pull-Up and Weak Pull-Down Resistor

Table 1–12 lists the weak pull-up and pull-down resistor values for Cyclone IV devices.

Table 1–12. Internal Weak Pull-Up and Weak Pull-Down Resistor Values for Cyclone IV Devices *(1)*

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{\_PU}$	Value of the I/O pin pull-up resistor before and during configuration, as well as user mode if you enable the programmable pull-up resistor option	V_{CCIO} = 3.3 V ± 5% *(2), (3)*	7	25	41	kΩ
		V_{CCIO} = 3.0 V ± 5% *(2), (3)*	7	28	47	kΩ
		V_{CCIO} = 2.5 V ± 5% *(2), (3)*	8	35	61	kΩ
		V_{CCIO} = 1.8 V ± 5% *(2), (3)*	10	57	108	kΩ
		V_{CCIO} = 1.5 V ± 5% *(2), (3)*	13	82	163	kΩ
		V_{CCIO} = 1.2 V ± 5% *(2), (3)*	19	143	351	kΩ
$R_{\_PD}$	Value of the I/O pin pull-down resistor before and during configuration	V_{CCIO} = 3.3 V ± 5% *(4)*	6	19	30	kΩ
		V_{CCIO} = 3.0 V ± 5% *(4)*	6	22	36	kΩ
		V_{CCIO} = 2.5 V ± 5% *(4)*	6	25	43	kΩ
		V_{CCIO} = 1.8 V ± 5% *(4)*	7	35	71	kΩ
		V_{CCIO} = 1.5 V ± 5% *(4)*	8	50	112	kΩ

Notes to Table 1–12:

(1) All I/O pins have an option to enable weak pull-up except the configuration, test, and JTAG pins. The weak pull-down feature is only available for JTAG `TCK`.

(2) Pin pull-up resistance values may be lower if an external source drives the pin higher than V_{CCIO}.

(3) $R_{\_PU} = (V_{CCIO} - V_I)/I_{R\_PU}$
Minimum condition: –40°C; $V_{CCIO} = V_{CC} + 5\%$, $V_I = V_{CC} + 5\% - 50$ mV;
Typical condition: 25°C; $V_{CCIO} = V_{CC}$, $V_I = 0$ V;
Maximum condition: 100°C; $V_{CCIO} = V_{CC} - 5\%$, $V_I = 0$ V; in which V_I refers to the input voltage at the I/O pin.

(4) $R_{\_PD} = V_I/I_{R\_PD}$
Minimum condition: –40°C; $V_{CCIO} = V_{CC} + 5\%$, $V_I = 50$ mV;
Typical condition: 25°C; $V_{CCIO} = V_{CC}$, $V_I = V_{CC} - 5\%$;
Maximum condition: 100°C; $V_{CCIO} = V_{CC} - 5\%$, $V_I = V_{CC} - 5\%$; in which V_I refers to the input voltage at the I/O pin.

Hot-Socketing

Table 1–13 lists the hot-socketing specifications for Cyclone IV devices.

Table 1–13. Hot-Socketing Specifications for Cyclone IV Devices

Symbol	Parameter	Maximum
$I_{IOPIN(DC)}$	DC current per I/O pin	300 μA
$I_{IOPIN(AC)}$	AC current per I/O pin	8 mA *(1)*
$I_{XCVRTX(DC)}$	DC current per transceiver `TX` pin	100 mA
$I_{XCVRRX(DC)}$	DC current per transceiver `RX` pin	50 mA

Note to Table 1–13:

(1) The I/O ramp rate is 10 ns or more. For ramp rates faster than 10 ns, |IIOPIN| = C dv/dt, in which C is the I/O pin capacitance and dv/dt is the slew rate.

☞ During hot-socketing, the I/O pin capacitance is less than 15 pF and the clock pin capacitance is less than 20 pF.

Figure 1–4 shows the differential receiver input waveform.

Figure 1–4. Receiver Input Waveform

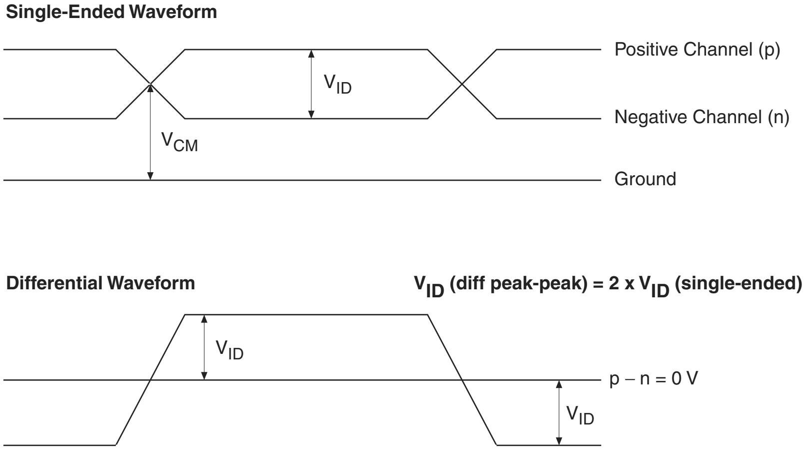


Figure 1–5 shows the transmitter output waveform.

Figure 1–5. Transmitter Output Waveform

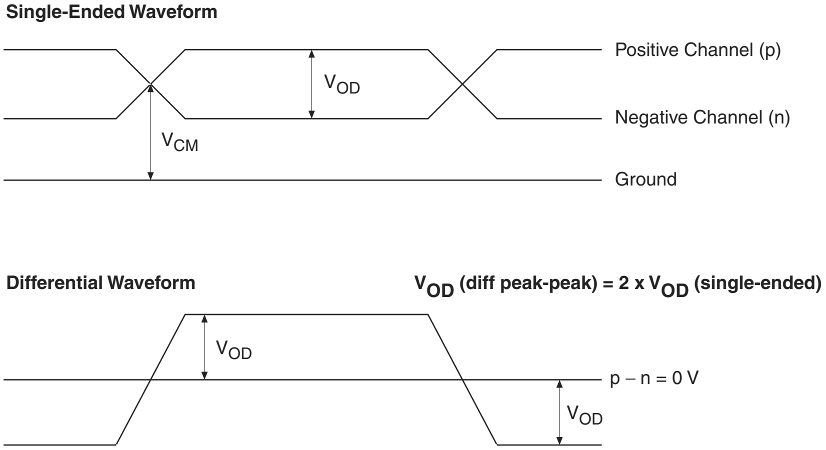


Table 1–22 lists the typical V_{OD} for Tx term that equals 100 Ω.

Table 1–22. Typical V_{OD} Setting, Tx Term = 100 Ω

Symbol	V_{OD} Setting (mV)					
	1	2	3	4 (1)	5	6
V_{OD} differential peak to peak typical (mV)	400	600	800	900	1000	1200

Note to Table 1–22:

(1) This setting is required for compliance with the PCIe protocol.

Table 1–24. Clock Tree Performance for Cyclone IV Devices ***(Part 2 of 2)***

Device	Performance								Unit
	C6	C7	C8	C8L *(1)*	C9L *(1)*	I7	I8L *(1)*	A7	
EP4CE55	500	437.5	402	362	265	437.5	362	—	MHz
EP4CE75	500	437.5	402	362	265	437.5	362	—	MHz
EP4CE115	—	437.5	402	362	265	437.5	362	—	MHz
EP4CGX15	500	437.5	402	—	—	437.5	—	—	MHz
EP4CGX22	500	437.5	402	—	—	437.5	—	—	MHz
EP4CGX30	500	437.5	402	—	—	437.5	—	—	MHz
EP4CGX50	500	437.5	402	—	—	437.5	—	—	MHz
EP4CGX75	500	437.5	402	—	—	437.5	—	—	MHz
EP4CGX110	500	437.5	402	—	—	437.5	—	—	MHz
EP4CGX150	500	437.5	402	—	—	437.5	—	—	MHz

Note to Table 1–24:

(1) Cyclone IV E 1.0 V core voltage devices only support C8L, C9L, and I8L speed grades.

PLL Specifications

Table 1–25 lists the PLL specifications for Cyclone IV devices when operating in the commercial junction temperature range (0°C to 85°C), the industrial junction temperature range (–40°C to 100°C), the extended industrial junction temperature range (–40°C to 125°C), and the automotive junction temperature range (–40°C to 125°C). For more information about the PLL block, refer to “Glossary” on page 1–37.

Table 1–25. PLL Specifications for Cyclone IV Devices *(1), (2)* **(Part 1 of 2)**

Symbol	Parameter	Min	Typ	Max	Unit
f_{IN} *(3)*	Input clock frequency (–6, –7, –8 speed grades)	5	—	472.5	MHz
	Input clock frequency (–8L speed grade)	5	—	362	MHz
	Input clock frequency (–9L speed grade)	5	—	265	MHz
f_{INPFD}	PFD input frequency	5	—	325	MHz
f_{VCO} *(4)*	PLL internal VCO operating range	600	—	1300	MHz
f_{INDUTY}	Input clock duty cycle	40	—	60	%
$t_{INJITTER\_CCJ}$ *(5)*	Input clock cycle-to-cycle jitter $F_{REF} \geq 100$ MHz	—	—	0.15	UI
	$F_{REF} < 100$ MHz	—	—	±750	ps
f_{OUT_EXT} (external clock output) *(3)*	PLL output frequency	—	—	472.5	MHz
f_{OUT} (to global clock)	PLL output frequency (–6 speed grade)	—	—	472.5	MHz
	PLL output frequency (–7 speed grade)	—	—	450	MHz
	PLL output frequency (–8 speed grade)	—	—	402.5	MHz
	PLL output frequency (–8L speed grade)	—	—	362	MHz
	PLL output frequency (–9L speed grade)	—	—	265	MHz
$t_{OUTDUTY}$	Duty cycle for external clock output (when set to 50%)	45	50	55	%
t_{LOCK}	Time required to lock from end of device configuration	—	—	1	ms

Embedded Multiplier Specifications

Table 1–26 lists the embedded multiplier specifications for Cyclone IV devices.

Table 1–26. Embedded Multiplier Specifications for Cyclone IV Devices

Mode	Resources Used	Performance					Unit
	Number of Multipliers	C6	C7, I7, A7	C8	C8L, I8L	C9L	
9 × 9-bit multiplier	1	340	300	260	240	175	MHz
18 × 18-bit multiplier	1	287	250	200	185	135	MHz

Memory Block Specifications

Table 1–27 lists the M9K memory block specifications for Cyclone IV devices.

Table 1–27. Memory Block Performance Specifications for Cyclone IV Devices

Memory	Mode	Resources Used		Performance					Unit
		LEs	M9K Memory	C6	C7, I7, A7	C8	C8L, I8L	C9L	
M9K Block	FIFO 256 × 36	47	1	315	274	238	200	157	MHz
	Single-port 256 × 36	0	1	315	274	238	200	157	MHz
	Simple dual-port 256 × 36 CLK	0	1	315	274	238	200	157	MHz
	True dual port 512 × 18 single CLK	0	1	315	274	238	200	157	MHz

Configuration and JTAG Specifications

Table 1–28 lists the configuration mode specifications for Cyclone IV devices.

Table 1–28. Passive Configuration Mode Specifications for Cyclone IV Devices *(1)*

Programming Mode	V_{CCINT} Voltage Level (V)	DCLK f_{MAX}	Unit
Passive Serial (PS)	1.0 *(3)*	66	MHz
	1.2	133	MHz
Fast Passive Parallel (FPP) *(2)*	1.0 *(3)*	66	MHz
	1.2 *(4)*	100	MHz

Notes to Table 1–28:

(1) For more information about PS and FPP configuration timing parameters, refer to the *Configuration and Remote System Upgrades in Cyclone IV Devices* chapter.

(2) FPP configuration mode supports all Cyclone IV E devices (except for E144 package devices) and EP4CGX50, EP4CGX75, EP4CGX110, and EP4CGX150 only.

(3) V_{CCINT} = 1.0 V is only supported for Cyclone IV E 1.0 V core voltage devices.

(4) Cyclone IV E devices support 1.2 V V_{CCINT}. Cyclone IV E 1.2 V core voltage devices support 133 MHz `DCLK` f_{MAX} for EP4CE6, EP4CE10, EP4CE15, EP4CE22, EP4CE30, and EP4CE40 only.

Table 1–29 lists the active configuration mode specifications for Cyclone IV devices.

Table 1–29. Active Configuration Mode Specifications for Cyclone IV Devices

Programming Mode	DCLK Range	Typical DCLK	Unit
Active Parallel (AP) (1)	20 to 40	33	MHz
Active Serial (AS)	20 to 40	33	MHz

Note to Table 1–29:

(1) AP configuration mode is only supported for Cyclone IV E devices.

Table 1–30 lists the JTAG timing parameters and values for Cyclone IV devices.

Table 1–30. JTAG Timing Parameters for Cyclone IV Devices (1)

Symbol	Parameter	Min	Max	Unit
t_{JCP}	TCK clock period	40	—	ns
t_{JCH}	TCK clock high time	19	—	ns
t_{JCL}	TCK clock low time	19	—	ns
t_{JPSU_TDI}	JTAG port setup time for TDI	1	—	ns
t_{JPSU_TMS}	JTAG port setup time for TMS	3	—	ns
t_{JPH}	JTAG port hold time	10	—	ns
t_{JPCO}	JTAG port clock to output (2), (3)	—	15	ns
t_{JPZX}	JTAG port high impedance to valid output (2), (3)	—	15	ns
t_{JPXZ}	JTAG port valid output to high impedance (2), (3)	—	15	ns
t_{JSSU}	Capture register setup time	5	—	ns
t_{JSH}	Capture register hold time	10	—	ns
t_{JSCO}	Update register clock to output	—	25	ns
t_{JSZX}	Update register high impedance to valid output	—	25	ns
t_{JSXZ}	Update register valid output to high impedance	—	25	ns

Notes to Table 1–30:

(1) For more information about JTAG waveforms, refer to “JTAG Waveform” in “Glossary” on page 1–37.

(2) The specification is shown for 3.3-, 3.0-, and 2.5-V LVTTL/LVCMOS operation of JTAG pins. For 1.8-V LVTTL/LVCMOS and 1.5-V LVCMOS, the output time specification is 16 ns.

(3) For EP4CGX22, EP4CGX30 (F324 and smaller package), EP4CGX110, and EP4CGX150 devices, the output time specification for 3.3-, 3.0-, and 2.5-V LVTTL/LVCMOS operation of JTAG pins is 16 ns. For 1.8-V LVTTL/LVCMOS and 1.5-V LVCMOS, the output time specification is 18 ns.

Periphery Performance

This section describes periphery performance, including high-speed I/O and external memory interface.

I/O performance supports several system interfaces, such as the high-speed I/O interface, external memory interface, and the PCI/PCI-X bus interface. I/Os using the SSTL-18 Class I termination standard can achieve up to the stated DDR2 SDRAM interfacing speeds. I/Os using general-purpose I/O standards such as 3.3-, 3.0-, 2.5-, 1.8-, or 1.5-LVTTL/LVCMOS are capable of a typical 200 MHz interfacing frequency with a 10 pF load.

Table 1–35. Emulated LVDS Transmitter Timing Specifications for Cyclone IV Devices *(1), (3)* **(Part 2 of 2)**

Symbol	Modes	C6		C7, I7		C8, A7		C8L, I8L		C9L		Unit
		Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
t_{DUTY}	—	45	55	45	55	45	55	45	55	45	55	%
TCCS	—	—	200	—	200	—	200	—	200	—	200	ps
Output jitter (peak to peak)	—	—	500	—	500	—	550	—	600	—	700	ps
t_{LOCK} *(2)*	—	—	1	—	1	—	1	—	1	—	1	ms

Notes to Table 1–35:

(1) Cyclone IV E—emulated LVDS transmitter is supported at the output pin of all I/O Banks.
Cyclone IV GX—emulated LVDS transmitter is supported at the output pin of I/O Banks 3, 4, 5, 6, 7, 8, and 9.

(2) t_{LOCK} is the time required for the PLL to lock from the end-of-device configuration.

(3) Cyclone IV E 1.0 V core voltage devices only support C8L, C9L, and I8L speed grades. Cyclone IV E 1.2 V core voltage devices only support C6, C7, C8, I7, and A7 speed grades. Cyclone IV GX devices only support C6, C7, C8, and I7 speed grades.

Table 1–36. LVDS Receiver Timing Specifications for Cyclone IV Devices *(1), (3)*

Symbol	Modes	C6		C7, I7		C8, A7		C8L, I8L		C9L		Unit
		Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
f_{HSCLK} (input clock frequency)	×10	10	437.5	10	370	10	320	10	320	10	250	MHz
	×8	10	437.5	10	370	10	320	10	320	10	250	MHz
	×7	10	437.5	10	370	10	320	10	320	10	250	MHz
	×4	10	437.5	10	370	10	320	10	320	10	250	MHz
	×2	10	437.5	10	370	10	320	10	320	10	250	MHz
	×1	10	437.5	10	402.5	10	402.5	10	362	10	265	MHz
HSIODR	×10	100	875	100	740	100	640	100	640	100	500	Mbps
	×8	80	875	80	740	80	640	80	640	80	500	Mbps
	×7	70	875	70	740	70	640	70	640	70	500	Mbps
	×4	40	875	40	740	40	640	40	640	40	500	Mbps
	×2	20	875	20	740	20	640	20	640	20	500	Mbps
	×1	10	437.5	10	402.5	10	402.5	10	362	10	265	Mbps
SW	—	—	400	—	400	—	400	—	550	—	640	ps
Input jitter tolerance	—	—	500	—	500	—	550	—	600	—	700	ps
t_{LOCK} *(2)*	—	—	1	—	1	—	1	—	1	—	1	ms

Notes to Table 1–36:

(1) Cyclone IV E—LVDS receiver is supported at all I/O Banks.
Cyclone IV GX—LVDS receiver is supported at I/O Banks 3, 4, 5, 6, 7, 8, and 9.

(2) t_{LOCK} is the time required for the PLL to lock from the end-of-device configuration.

(3) Cyclone IV E 1.0 V core voltage devices only support C8L, C9L, and I8L speed grades. Cyclone IV E 1.2 V core voltage devices only support C6, C7, C8, I7, and A7 speed grades. Cyclone IV GX devices only support C6, C7, C8, and I7 speed grades.

External Memory Interface Specifications

The external memory interfaces for Cyclone IV devices are auto-calibrating and easy to implement.

IOE Programmable Delay

Table 1–40 and Table 1–41 list the IOE programmable delay for Cyclone IV E 1.0 V core voltage devices.

Table 1–40. IOE Programmable Delay on Column Pins for Cyclone IV E 1.0 V Core Voltage Devices *(1), (2)*

Parameter	Paths Affected	Number of Setting	Min Offset	Max Offset					Unit
				Fast Corner		Slow Corner			
				C8L	I8L	C8L	C9L	I8L	
Input delay from pin to internal cells	Pad to I/O dataout to core	7	0	2.054	1.924	3.387	4.017	3.411	ns
Input delay from pin to input register	Pad to I/O input register	8	0	2.010	1.875	3.341	4.252	3.367	ns
Delay from output register to output pin	I/O output register to pad	2	0	0.641	0.631	1.111	1.377	1.124	ns
Input delay from dual-purpose clock pin to fan-out destinations	Pad to global clock network	12	0	0.971	0.931	1.684	2.298	1.684	ns

Notes to Table 1–40:

(1) The incremental values for the settings are generally linear. For the exact values for each setting, use the latest version of the Quartus II software.

(2) The minimum and maximum offset timing numbers are in reference to setting **0** as available in the Quartus II software.

Table 1–41. IOE Programmable Delay on Row Pins for Cyclone IV E 1.0 V Core Voltage Devices *(1), (2)*

Parameter	Paths Affected	Number of Setting	Min Offset	Max Offset					Unit
				Fast Corner		Slow Corner			
				C8L	I8L	C8L	C9L	I8L	
Input delay from pin to internal cells	Pad to I/O dataout to core	7	0	2.057	1.921	3.389	4.146	3.412	ns
Input delay from pin to input register	Pad to I/O input register	8	0	2.059	1.919	3.420	4.374	3.441	ns
Delay from output register to output pin	I/O output register to pad	2	0	0.670	0.623	1.160	1.420	1.168	ns
Input delay from dual-purpose clock pin to fan-out destinations	Pad to global clock network	12	0	0.960	0.919	1.656	2.258	1.656	ns

Notes to Table 1–41:

(1) The incremental values for the settings are generally linear. For the exact values for each setting, use the latest version of the Quartus II software.

(2) The minimum and maximum offset timing numbers are in reference to setting **0** as available in the Quartus II software.

Table 1–42 and Table 1–43 list the IOE programmable delay for Cyclone IV E 1.2 V core voltage devices.

Table 1–42. IOE Programmable Delay on Column Pins for Cyclone IV E 1.2 V Core Voltage Devices *(1), (2)*

Parameter	Paths Affected	Number of Setting	Min Offset	Max Offset								Unit
				Fast Corner			Slow Corner					
				C6	I7	A7	C6	C7	C8	I7	A7	
Input delay from pin to internal cells	Pad to I/O dataout to core	7	0	1.314	1.211	1.211	2.177	2.340	2.433	2.388	2.508	ns
Input delay from pin to input register	Pad to I/O input register	8	0	1.307	1.203	1.203	2.19	2.387	2.540	2.430	2.545	ns
Delay from output register to output pin	I/O output register to pad	2	0	0.437	0.402	0.402	0.747	0.820	0.880	0.834	0.873	ns
Input delay from dual-purpose clock pin to fan-out destinations	Pad to global clock network	12	0	0.693	0.665	0.665	1.200	1.379	1.532	1.393	1.441	ns

Notes to Table 1–42:

(1) The incremental values for the settings are generally linear. For the exact values for each setting, use the latest version of the Quartus II software.

(2) The minimum and maximum offset timing numbers are in reference to setting **0** as available in the Quartus II software.

Table 1–43. IOE Programmable Delay on Row Pins for Cyclone IV E 1.2 V Core Voltage Devices *(1), (2)*

Parameter	Paths Affected	Number of Setting	Min Offset	Max Offset								Unit
				Fast Corner			Slow Corner					
				C6	I7	A7	C6	C7	C8	I7	A7	
Input delay from pin to internal cells	Pad to I/O dataout to core	7	0	1.314	1.209	1.209	2.201	2.386	2.510	2.429	2.548	ns
Input delay from pin to input register	Pad to I/O input register	8	0	1.312	1.207	1.207	2.202	2.402	2.558	2.447	2.557	ns
Delay from output register to output pin	I/O output register to pad	2	0	0.458	0.419	0.419	0.783	0.861	0.924	0.875	0.915	ns
Input delay from dual-purpose clock pin to fan-out destinations	Pad to global clock network	12	0	0.686	0.657	0.657	1.185	1.360	1.506	1.376	1.422	ns

Notes to Table 1–43:

(1) The incremental values for the settings are generally linear. For the exact values for each setting, use the latest version of the Quartus II software.

(2) The minimum and maximum offset timing numbers are in reference to setting **0** as available in the Quartus II software.

Table 1–44 and Table 1–45 list the IOE programmable delay for Cyclone IV GX devices.

Table 1–44. IOE Programmable Delay on Column Pins for Cyclone IV GX Devices (1), (2)

Parameter	Paths Affected	Number of Settings	Min Offset	Max Offset						Unit
				Fast Corner		Slow Corner				
				C6	I7	C6	C7	C8	I7	
Input delay from pin to internal cells	Pad to I/O dataout to core	7	0	1.313	1.209	2.184	2.336	2.451	2.387	ns
Input delay from pin to input register	Pad to I/O input register	8	0	1.312	1.208	2.200	2.399	2.554	2.446	ns
Delay from output register to output pin	I/O output register to pad	2	0	0.438	0.404	0.751	0.825	0.886	0.839	ns
Input delay from dual-purpose clock pin to fan-out destinations	Pad to global clock network	12	0	0.713	0.682	1.228	1.41	1.566	1.424	ns

Notes to Table 1–44:

(1) The incremental values for the settings are generally linear. For exact values of each setting, use the latest version of the Quartus II software.

(2) The minimum and maximum offset timing numbers are in reference to setting **0** as available in the Quartus II software.

Table 1–45. IOE Programmable Delay on Row Pins for Cyclone IV GX Devices (1), (2)

Parameter	Paths Affected	Number of Settings	Min Offset	Max Offset						Unit
				Fast Corner		Slow Corner				
				C6	I7	C6	C7	C8	I7	
Input delay from pin to internal cells	Pad to I/O dataout to core	7	0	1.314	1.210	2.209	2.398	2.526	2.443	ns
Input delay from pin to input register	Pad to I/O input register	8	0	1.313	1.208	2.205	2.406	2.563	2.450	ns
Delay from output register to output pin	I/O output register to pad	2	0	0.461	0.421	0.789	0.869	0.933	0.884	ns
Input delay from dual-purpose clock pin to fan-out destinations	Pad to global clock network	12	0	0.712	0.682	1.225	1.407	1.562	1.421	ns

Notes to Table 1–45:

(1) The incremental values for the settings are generally linear. For exact values of each setting, use the latest version of Quartus II software.

(2) The minimum and maximum offset timing numbers are in reference to setting **0** as available in the Quartus II software

I/O Timing

Use the following methods to determine I/O timing:

- the Excel-based I/O Timing
- the Quartus II timing analyzer

The Excel-based I/O timing provides pin timing performance for each device density and speed grade. The data is typically used prior to designing the FPGA to get a timing budget estimation as part of the link timing analysis. The Quartus II timing analyzer provides a more accurate and precise I/O timing data based on the specifics of the design after place-and-route is complete.

The Excel-based I/O Timing spreadsheet is downloadable from Cyclone IV Devices Literature website.

Glossary

Table 1–46 lists the glossary for this chapter.

Table 1–46. Glossary (Part 1 of 5)

Letter	Term	Definitions
A	—	—
B	—	—
C	—	—
D	—	—
E	—	—
F	f_{HSCLK}	High-speed I/O block: High-speed receiver/transmitter input and output clock frequency.
G	GCLK	Input pin directly to Global Clock network.
	GCLK PLL	Input pin to Global Clock network through the PLL.
H	HSIODR	High-speed I/O block: Maximum/minimum LVDS data transfer rate (HSIODR = 1/TUI).
I	Input Waveforms for the SSTL Differential I/O Standard	

Table 1–46. Glossary (Part 2 of 5)

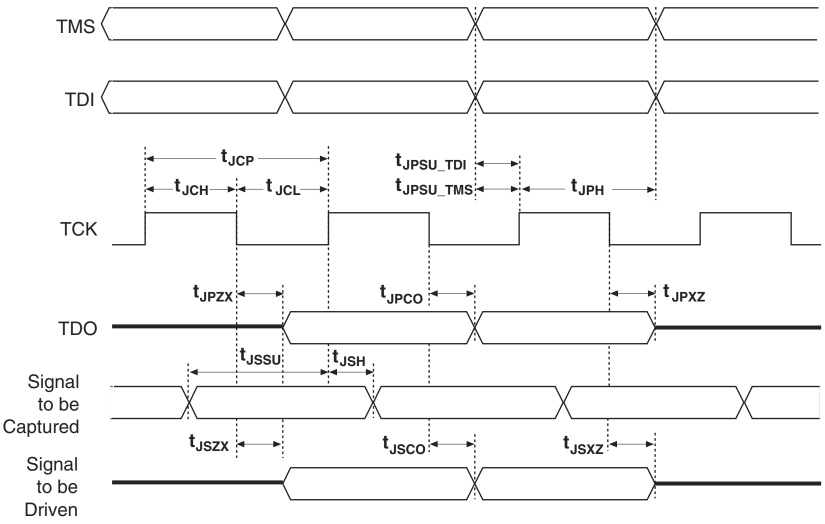
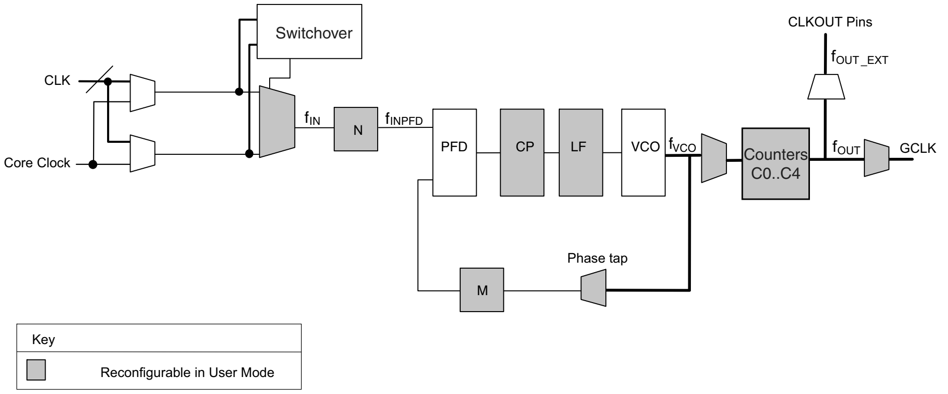
<table>
<tr><th>Letter</th><th>Term</th><th>Definitions</th></tr>
<tr><td>J</td><td>JTAG Waveform</td><td>
</td></tr>
<tr><td>K</td><td>—</td><td>—</td></tr>
<tr><td>L</td><td>—</td><td>—</td></tr>
<tr><td>M</td><td>—</td><td>—</td></tr>
<tr><td>N</td><td>—</td><td>—</td></tr>
<tr><td>O</td><td>—</td><td>—</td></tr>
<tr><td>P</td><td>PLL Block</td><td>The following highlights the PLL specification parameters:

</td></tr>
<tr><td>Q</td><td>—</td><td>—</td></tr>
</table>

Table 1–46. Glossary (Part 4 of 5)

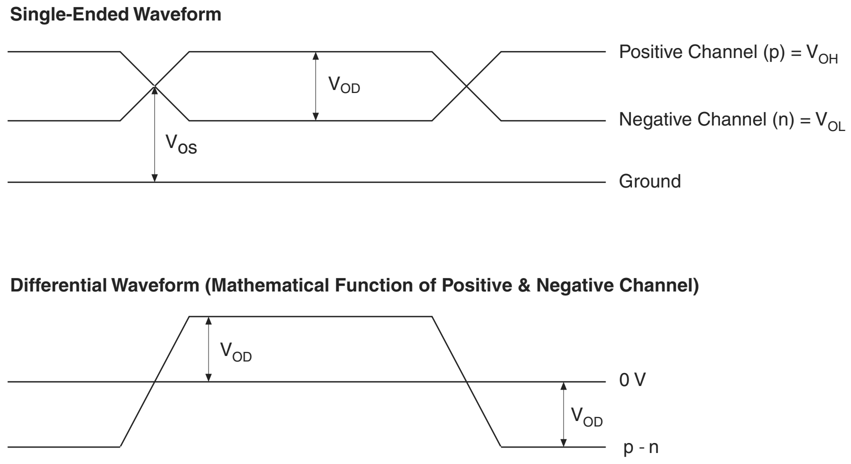
Letter	Term	Definitions
T	t_C	High-speed receiver and transmitter input and output clock period.
	Channel-to-channel-skew (TCCS)	High-speed I/O block: The timing difference between the fastest and slowest output edges, including t_{CO} variation and clock skew. The clock is included in the TCCS measurement.
	t_{cin}	Delay from the clock pad to the I/O input register.
	t_{CO}	Delay from the clock pad to the I/O output.
	t_{cout}	Delay from the clock pad to the I/O output register.
	t_{DUTY}	High-speed I/O block: Duty cycle on high-speed transmitter output clock.
	t_{FALL}	Signal high-to-low transition time (80–20%).
	t_H	Input register hold time.
	Timing Unit Interval (TUI)	High-speed I/O block: The timing budget allowed for skew, propagation delays, and data sampling window. (TUI = 1/(Receiver Input Clock Frequency Multiplication Factor) = t_C/w).
	$t_{INJITTER}$	Period jitter on the PLL clock input.
	$t_{OUTJITTER\_DEDCLK}$	Period jitter on the dedicated clock output driven by a PLL.
	$t_{OUTJITTER\_IO}$	Period jitter on the general purpose I/O driven by a PLL.
	t_{pllcin}	Delay from the PLL inclk pad to the I/O input register.
	$t_{pllcout}$	Delay from the PLL inclk pad to the I/O output register.
	Transmitter Output Waveform	Transmitter output waveforms for the LVDS, mini-LVDS, PPDS and RSDS Differential I/O Standards: 
	t_{RISE}	Signal low-to-high transition time (20–80%).
	t_{SU}	Input register setup time.
U	—	—

Table 1–46. Glossary (Part 5 of 5)

Letter	Term	Definitions
V	$V_{CM(DC)}$	DC common mode input voltage.
	$V_{DIF(AC)}$	AC differential input voltage: The minimum AC input differential voltage required for switching.
	$V_{DIF(DC)}$	DC differential input voltage: The minimum DC input differential voltage required for switching.
	V_{ICM}	Input common mode voltage: The common mode of the differential signal at the receiver.
	V_{ID}	Input differential voltage swing: The difference in voltage between the positive and complementary conductors of a differential transmission at the receiver.
	V_{IH}	Voltage input high: The minimum positive voltage applied to the input that is accepted by the device as a logic high.
	$V_{IH(AC)}$	High-level AC input voltage.
	$V_{IH(DC)}$	High-level DC input voltage.
	V_{IL}	Voltage input low: The maximum positive voltage applied to the input that is accepted by the device as a logic low.
	$V_{IL\ (AC)}$	Low-level AC input voltage.
	$V_{IL\ (DC)}$	Low-level DC input voltage.
	V_{IN}	DC input voltage.
	V_{OCM}	Output common mode voltage: The common mode of the differential signal at the transmitter.
	V_{OD}	Output differential voltage swing: The difference in voltage between the positive and complementary conductors of a differential transmission at the transmitter. $V_{OD} = V_{OH} – V_{OL}$.
	V_{OH}	Voltage output high: The maximum positive voltage from an output that the device considers is accepted as the minimum positive high level.
	V_{OL}	Voltage output low: The maximum positive voltage from an output that the device considers is accepted as the maximum positive low level.
	V_{OS}	Output offset voltage: $V_{OS} = (V_{OH} + V_{OL}) / 2$.
	$V_{OX\ (AC)}$	AC differential output cross point voltage: the voltage at which the differential output signals must cross.
	V_{REF}	Reference voltage for the SSTL and HSTL I/O standards.
	$V_{REF\ (AC)}$	AC input reference voltage for the SSTL and HSTL I/O standards. $V_{REF(AC)} = V_{REF(DC)}$ + noise. The peak-to-peak AC noise on V_{REF} must not exceed 2% of $V_{REF(DC)}$.
	$V_{REF\ (DC)}$	DC input reference voltage for the SSTL and HSTL I/O standards.
	$V_{SWING\ (AC)}$	AC differential input voltage: AC input differential voltage required for switching. For the SSTL differential I/O standard, refer to Input Waveforms.
	$V_{SWING\ (DC)}$	DC differential input voltage: DC input differential voltage required for switching. For the SSTL differential I/O standard, refer to Input Waveforms.
	V_{TT}	Termination voltage for the SSTL and HSTL I/O standards.
	$V_{X\ (AC)}$	AC differential input cross point voltage: The voltage at which the differential input signals must cross.
W	—	—
X	—	—
Y	—	—
Z	—	—